

# FDS7766S

## 30V N-Channel PowerTrench<sup>®</sup> MOSFET

### General Description

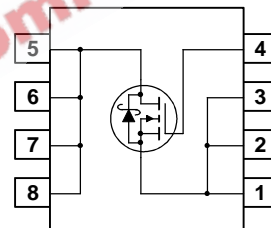
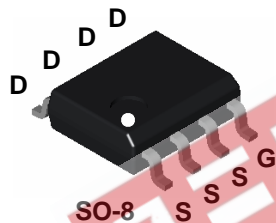
The FDS7766S is designed to replace a single SO-8 MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low  $R_{DS(ON)}$  and low gate charge. The FDS7766S includes an integrated Schottky diode using Fairchild's monolithic SyncFET technology.

### Applications

- Synchronous rectifier
- DC/DC converter

### Features

- 17 A, 30 V  $R_{DS(ON)} = 5.5 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(ON)} = 6.5 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$
- High performance trench technology for extremely low  $R_{DS(ON)}$
- High power and current handling capability
- Fast switching



### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage	30	V
V <sub>GSS</sub>	Gate-Source Voltage	±16	V
I <sub>D</sub>	Drain Current – Continuous (Note 1a)	17	A
	– Pulsed	60	
P <sub>D</sub>	Power Dissipation for Single Operation (Note 1a)	2.5	W
	(Note 1b)	1.2	
	(Note 1c)	1.0	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1c)	125	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Note 1)	25	°C/W

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS7766S	FDS7766S	13"	12mm	2500 units

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 15\text{ mA}$ , Referenced to $25^\circ\text{C}$		23		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			500	$\mu\text{A}$
$I_{GSS}$	Gate–Body Leakage	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1	1.3	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 15\text{ mA}$ , Referenced to $25^\circ\text{C}$		-2		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10\text{ V}, I_D = 17\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 15.5\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 17\text{ A}, T_J = 125^\circ\text{C}$		4.0 4.6 5.7	5.5 6.5 7.2	m $\Omega$
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	30			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 17\text{ A}$		91		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}$		4785		pF
$C_{oss}$	Output Capacitance	$f = 1.0\text{ MHz}$		825		pF
$C_{riss}$	Reverse Transfer Capacitance			290		pF
$R_G$	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$		1.3		$\Omega$

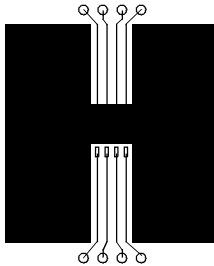
### Switching Characteristics (Note 2)

$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A}$		12	22	ns
$t_r$	Turn–On Rise Time	$V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		12	22	ns
$t_{d(off)}$	Turn–Off Delay Time			82	132	ns
$t_f$	Turn–Off Fall Time			30	49	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 17\text{ A}$ $V_{GS} = 5\text{ V}$		41	58	nC
$Q_{gs}$	Gate–Source Charge			11		nC
$Q_{gd}$	Gate–Drain Charge			9		nC

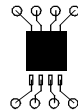
### Drain–Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain–Source Diode Forward Current				3.5	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.5\text{ A}$ (Note 2)		0.4	0.7	V
$t_{rr}$	Schottky Diode Reverse Recovery	$I_F = 17\text{ A}$ , $d_I/d_t = 300\text{ A}/\mu\text{s}$ (Note 2)		27		ns
$Q_{rr}$				28		nC

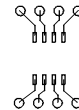
**Notes:** 1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $50^\circ\text{C}/\text{W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper



b)  $105^\circ\text{C}/\text{W}$  when mounted on a  $.04\text{ in}^2$  pad of 2 oz copper



c)  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width <  $300\mu\text{s}$ , Duty Cycle < 2.0%

Typical Characteristics

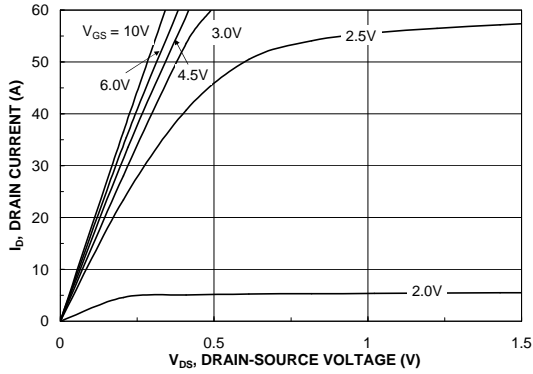


Figure 1. On-Region Characteristics.

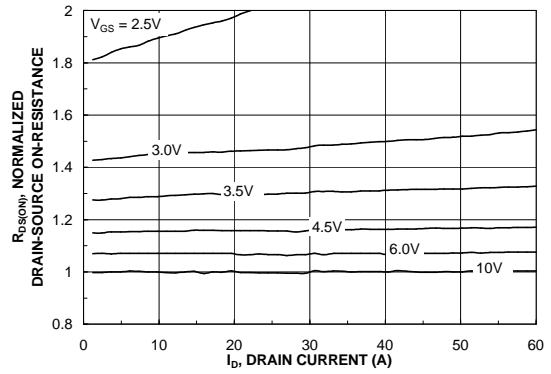


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

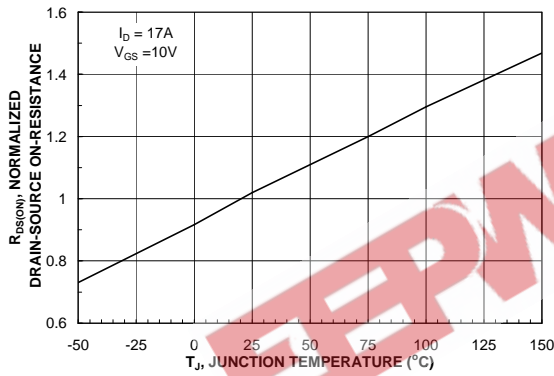


Figure 3. On-Resistance Variation with Temperature.

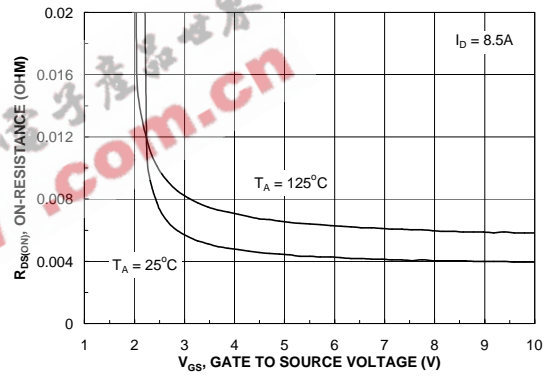


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

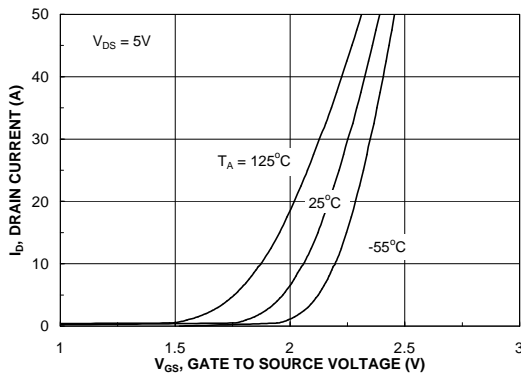


Figure 5. Transfer Characteristics.

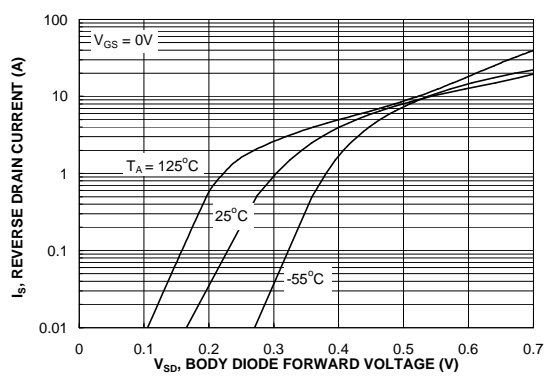


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

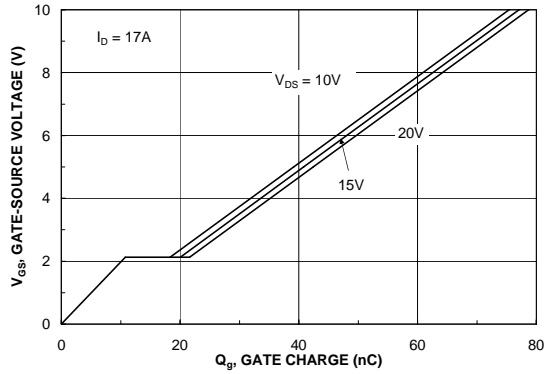


Figure 7. Gate Charge Characteristics.

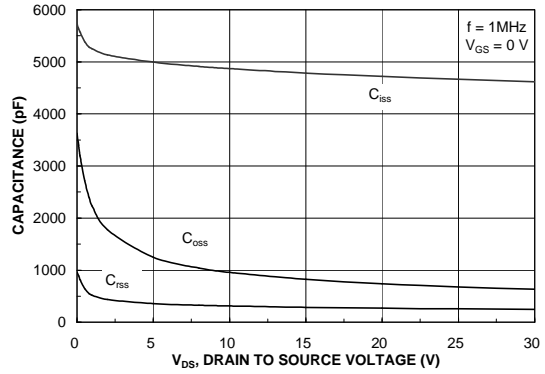


Figure 8. Capacitance Characteristics.

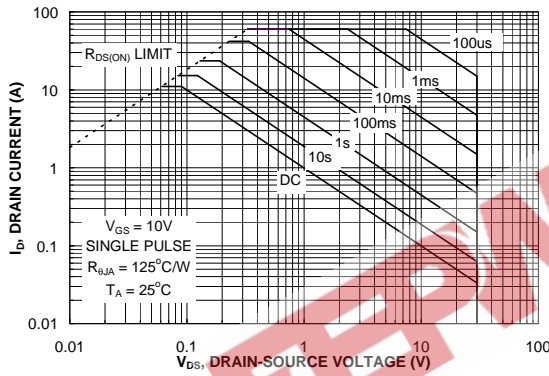


Figure 9. Maximum Safe Operating Area.

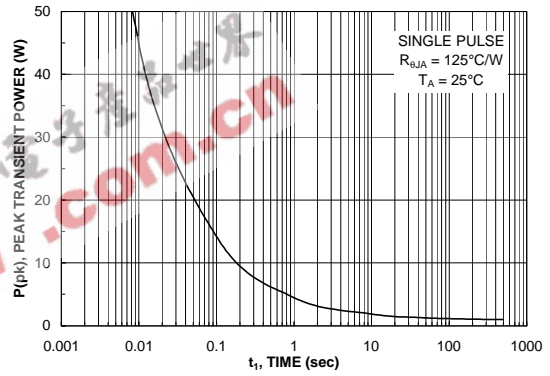


Figure 10. Single Pulse Maximum Power Dissipation.

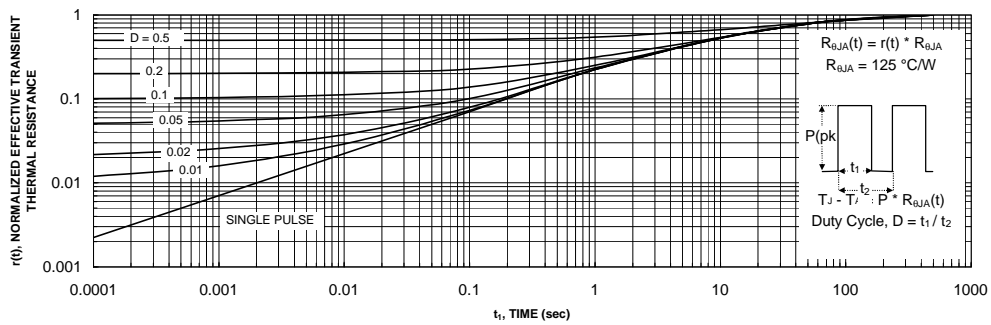


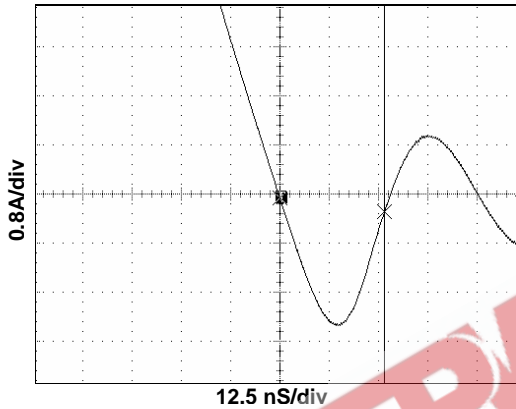
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

**Typical Characteristics** (continued)

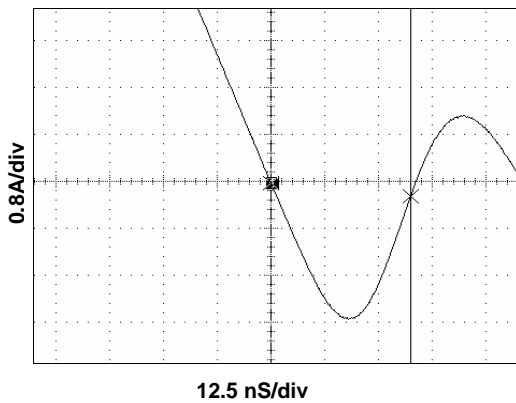
**SyncFET Schottky Body Diode Characteristics**

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDS7766S.



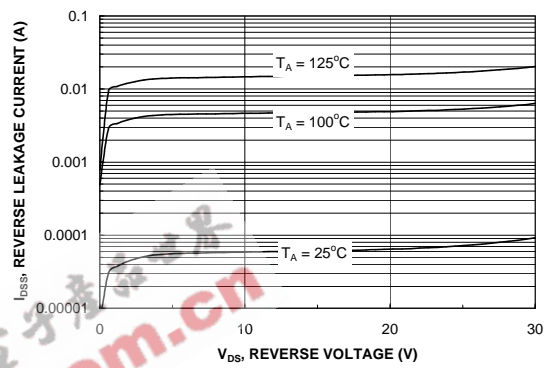
**Figure 12. FDS7766S SyncFET body diode reverse recovery characteristic.**

For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDS7766).



**Figure 13. Non-SyncFET (FDS7766) body diode reverse recovery characteristic.**

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.



**Figure 14. SyncFET body diode reverse leakage versus drain-source voltage and temperature**

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